

# DATA SHEET



## **PMBTA92** PNP high-voltage transistor

Product data sheet  
Supersedes data of 1999 Apr 13

2004 Jan 22

# PNP high-voltage transistor

# PMBTA92

### FEATURES

- Low current (max. 100 mA)
- High voltage (max. 300 V).

### APPLICATIONS

- Telephony
- Professional communication equipment.

### DESCRIPTION

PNP high-voltage transistor in a SOT23 plastic package.  
NPN complement: PMBTA42.

### MARKING

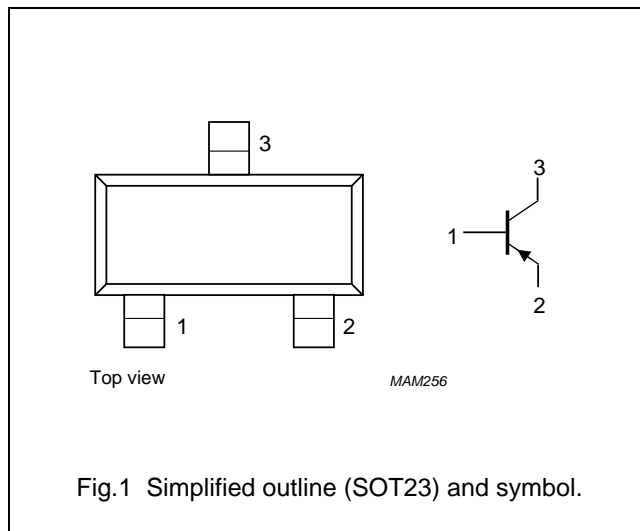
TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PMBTA92	*2D

### Note

- \* = p : Made in Hong Kong.  
\* = t : Made in Malaysia.  
\* = W : Made in China.

### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



### ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PMBTA92	–	plastic surface mounted package; 3 leads	SOT23

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	–	–300	V
V <sub>CEO</sub>	collector-emitter voltage	open base	–	–300	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	–5	V
I <sub>C</sub>	collector current (DC)		–	–100	mA
I <sub>CM</sub>	peak collector current		–	–200	mA
I <sub>BM</sub>	peak base current		–	–100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	–	250	mW
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

### Note

1. Transistor mounted on an FR4 printed-circuit board.

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## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

## Note

1. Transistor mounted on an FR4 printed-circuit board.

## CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = -200\text{ V}$	–	–250	nA
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = -3\text{ V}$	–	–100	nA
$h_{FE}$	DC current gain	$V_{CE} = -10\text{ V}$ ; note 1 $I_C = -1\text{ mA}$ $I_C = -10\text{ mA}$ $I_C = -30\text{ mA}$	25 40 25	– – –	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -20\text{ mA}; I_B = -2\text{ mA}$	–	–500	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -20\text{ mA}; I_B = -2\text{ mA}$	–	–900	mV
$C_c$	collector capacitance	$I_E = I_e = 0; V_{CB} = -20\text{ V}; f = 1\text{ MHz}$	–	6	pF
$f_T$	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -20\text{ V}; f = 100\text{ MHz}$	50	–	MHz

## Note

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

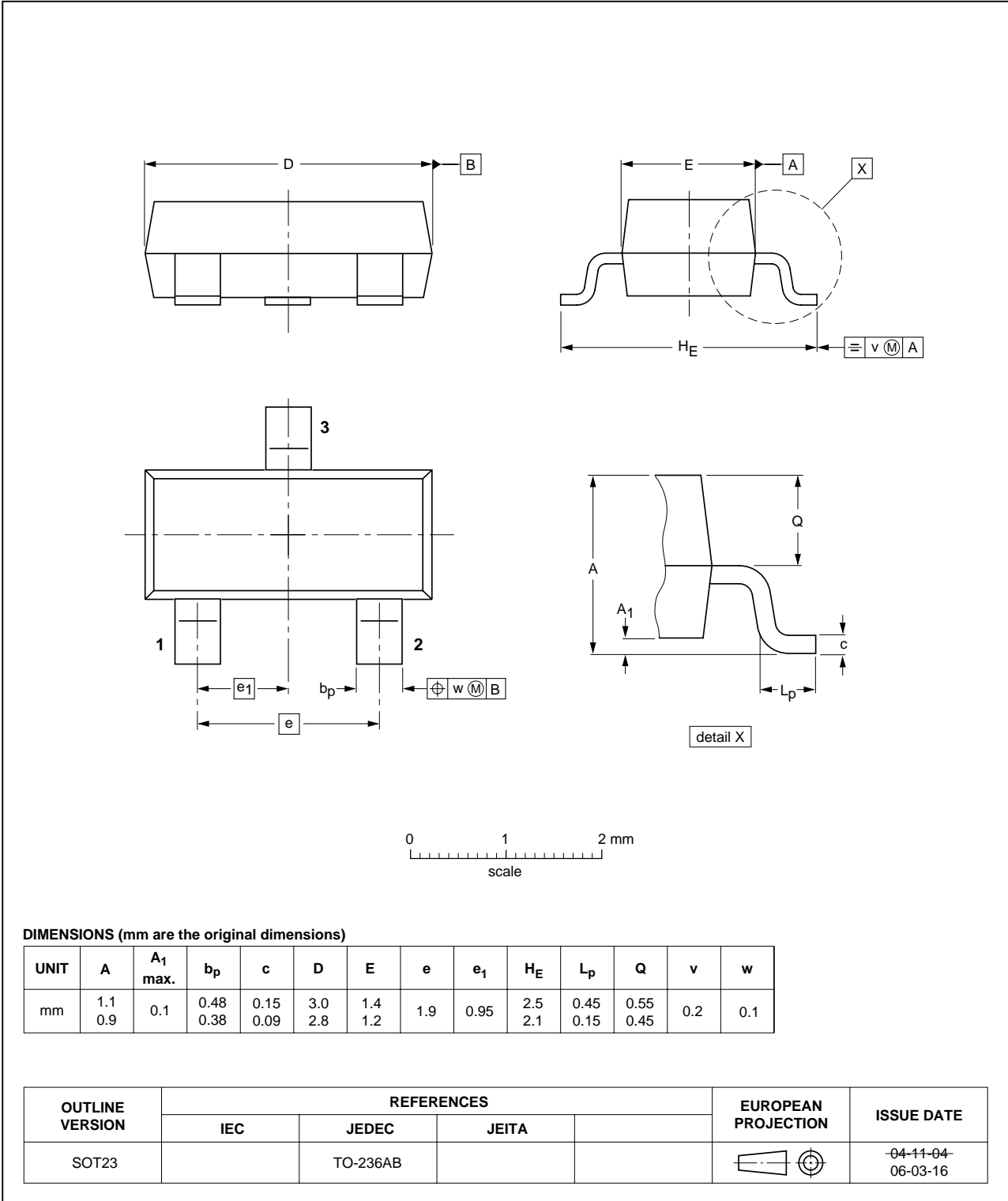
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PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



## PNP high-voltage transistor

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## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

## Notes

1. Please consult the most recently issued document before initiating or completing a design.
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# ***NXP Semiconductors***

## **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

## **Contact information**

For additional information please visit: <http://www.nxp.com>

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